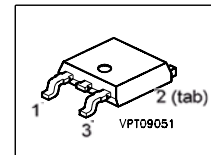


Cool MOS™ Power Transistor
Feature

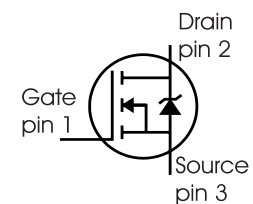
- New revolutionary high voltage technology
- Ultra low gate charge
- Periodic avalanche rated
- Extreme dv/dt rated
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC⁰⁾ for target applications

| | | |
|--------------|-----|----------|
| V_{DS} | 800 | V |
| $R_{DS(on)}$ | 2.7 | Ω |
| I_D | 2 | A |

PG-TO252



| Type | Package | Ordering Code | Marking |
|------------|----------|---------------|---------|
| SPD02N80C3 | PG-TO252 | Q67040-S4635 | 02N80C3 |


Maximum Ratings

| Parameter | Symbol | Value | Unit |
|---|---------------------|-------------|------|
| Continuous drain current | I_D | 2 | A |
| $T_C = 25\text{ °C}$ | | | |
| $T_C = 100\text{ °C}$ | | | |
| Pulsed drain current, t_p limited by T_{jmax} | $I_{D\text{ puls}}$ | 6 | |
| Avalanche energy, single pulse | E_{AS} | 90 | mJ |
| $I_D = 1\text{ A}, V_{DD} = 50\text{ V}$ | | | |
| Avalanche energy, repetitive t_{AR} limited by T_{jmax} ¹⁾ | E_{AR} | 0.05 | |
| $I_D = 2\text{ A}, V_{DD} = 50\text{ V}$ | | | |
| Avalanche current, repetitive t_{AR} limited by T_{jmax} | I_{AR} | 2 | A |
| Gate source voltage | V_{GS} | ± 20 | V |
| Gate source voltage AC ($f > 1\text{ Hz}$) | V_{GS} | ± 30 | |
| Power dissipation, $T_C = 25\text{ °C}$ | P_{tot} | 42 | W |
| Operating and storage temperature | T_j, T_{stg} | -55... +150 | °C |

Maximum Ratings

| Parameter | Symbol | Value | Unit |
|---|---------|-------|------|
| Drain Source voltage slope $V_{DS} = 640 \text{ V}, I_D = 2 \text{ A}, T_j = 125 \text{ }^\circ\text{C}$ | dv/dt | 50 | V/ns |

Thermal Characteristics

| Parameter | Symbol | Values | | | Unit |
|---|------------|--------|------|------|------|
| | | min. | typ. | max. | |
| Thermal resistance, junction - case | R_{thJC} | - | - | 3 | K/W |
| SMD version, device on PCB: @ min. footprint | R_{thJA} | - | - | 75 | |
| @ 6 cm ² cooling area ²⁾ | | - | - | 50 | |
| Soldering temperature, reflow soldering, MSL3 1.6 mm (0.063 in.) from case for 10s | T_{sold} | - | - | 260 | °C |

Electrical Characteristics, at $T_j=25^\circ\text{C}$ unless otherwise specified

| Parameter | Symbol | Conditions | Values | | | Unit |
|---|---------------|---|--------|------|------|---------------|
| | | | min. | typ. | max. | |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | $V_{GS}=0\text{V}, I_D=0.25\text{mA}$ | 800 | - | - | V |
| Drain-Source avalanche breakdown voltage | $V_{(BR)DS}$ | $V_{GS}=0\text{V}, I_D=2\text{A}$ | - | 870 | - | |
| Gate threshold voltage | $V_{GS(th)}$ | $I_D=120\mu\text{A}, V_{GS}=V_{DS}$ | 2.1 | 3 | 3.9 | |
| Zero gate voltage drain current | I_{DSS} | $V_{DS}=800\text{V}, V_{GS}=0\text{V},$ $T_j=25^\circ\text{C},$ $T_j=150^\circ\text{C}$ | - | 0.5 | 5 | μA |
| | | | - | - | 50 | |
| Gate-source leakage current | I_{GSS} | $V_{GS}=20\text{V}, V_{DS}=0\text{V}$ | - | - | 100 | nA |
| Drain-source on-state resistance | $R_{DS(on)}$ | $V_{GS}=10\text{V}, I_D=1.2\text{A},$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$ | - | 2.4 | 2.7 | Ω |
| | | | - | 6.5 | - | |
| Gate input resistance | R_G | $f=1\text{MHz}, \text{open Drain}$ | - | 0.7 | - | |

Electrical Characteristics , at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Values | | | Unit |
|---|--------------|--|--------|------|------|------|
| | | | min. | typ. | max. | |
| Transconductance | g_{fs} | $V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 1.2\text{A}$ | - | 1.5 | - | S |
| Input capacitance | C_{iss} | $V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$ | - | 290 | - | pF |
| Output capacitance | C_{oss} | | - | 130 | - | |
| Reverse transfer capacitance | C_{rss} | | - | 6 | - | |
| Effective output capacitance, ³⁾ energy related | $C_{o(er)}$ | $V_{GS} = 0\text{V}$, $V_{DS} = 0\text{V to } 480\text{V}$ | - | 11.2 | - | pF |
| Effective output capacitance, ⁴⁾ time related | $C_{o(tr)}$ | | - | 20.6 | - | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD} = 400\text{V}$, $V_{GS} = 0/10\text{V}$, $I_D = 2\text{A}$, $R_G = 47\Omega$ | - | 25 | - | ns |
| Rise time | t_r | | - | 15 | - | |
| Turn-off delay time | $t_{d(off)}$ | | - | 65 | 75 | |
| Fall time | t_f | | - | 18 | 23 | |

Gate Charge Characteristics

| | | | | | | |
|-----------------------|-----------------|--|---|---|----|----|
| Gate to source charge | Q_{gs} | $V_{DD} = 640\text{V}$, $I_D = 2\text{A}$ | - | 1 | - | nC |
| Gate to drain charge | Q_{gd} | | - | 5 | - | |
| Gate charge total | Q_g | $V_{DD} = 640\text{V}$, $I_D = 2\text{A}$, $V_{GS} = 0\text{ to } 10\text{V}$ | - | 9 | 12 | |
| Gate plateau voltage | $V_{(plateau)}$ | $V_{DD} = 640\text{V}$, $I_D = 2\text{A}$ | - | 6 | - | V |

⁰J-STD20 and JESD22

¹Repetitive avalanche causes additional power losses that can be calculated as $P_{AV} = E_{AR} \cdot f$.

²Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

³ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

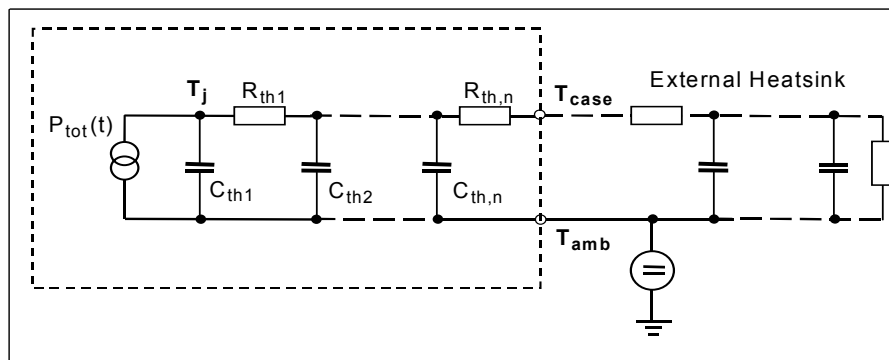
⁴ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

Electrical Characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Values | | | Unit |
|---|--------------|-----------------------------------|--------|------|------|------------------------|
| | | | min. | typ. | max. | |
| Inverse diode continuous forward current | I_S | $T_C=25^\circ\text{C}$ | - | - | 2 | A |
| Inverse diode direct current, pulsed | I_{SM} | | - | - | 6 | |
| Inverse diode forward voltage | V_{SD} | $V_{GS}=0\text{V}, I_F=I_S$ | - | 1 | 1.2 | V |
| Reverse recovery time | t_{rr} | $V_R=640\text{V}, I_F=I_S,$ | - | 520 | - | ns |
| Reverse recovery charge | Q_{rr} | $di_F/dt=100\text{A}/\mu\text{s}$ | - | 2 | - | μC |
| Peak reverse recovery current | I_{rrm} | | - | 6 | - | A |
| Peak rate of fall of reverse recovery current | di_{rr}/dt | | - | 200 | - | $\text{A}/\mu\text{s}$ |

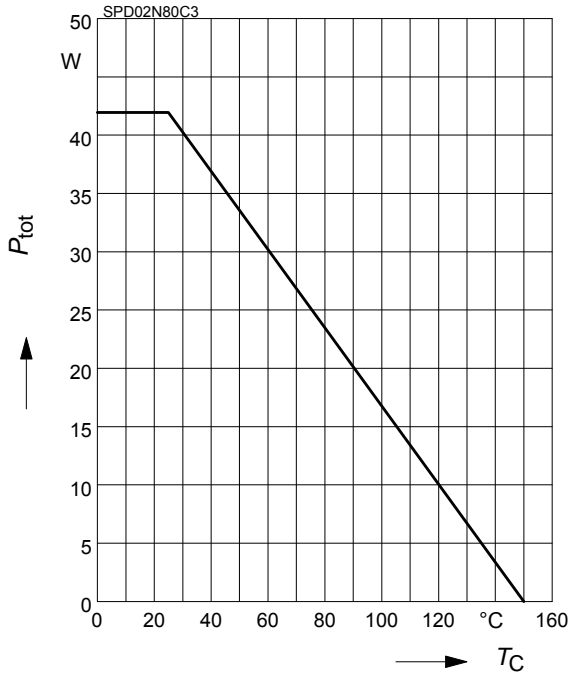
Typical Transient Thermal Characteristics

| Symbol | Value | Unit | Symbol | Value | Unit |
|--------------------|-------|------|---------------------|------------|------|
| | typ. | | | typ. | |
| Thermal resistance | | | Thermal capacitance | | |
| R_{th1} | 0.067 | K/W | C_{th1} | 0.00004221 | Ws/K |
| R_{th2} | 0.126 | | C_{th2} | 0.0001651 | |
| R_{th3} | 0.215 | | C_{th3} | 0.0002432 | |
| R_{th4} | 0.655 | | C_{th4} | 0.0007613 | |
| R_{th5} | 0.569 | | C_{th5} | 0.002455 | |
| R_{th6} | 0.161 | | C_{th6} | 0.412 | |



1 Power dissipation

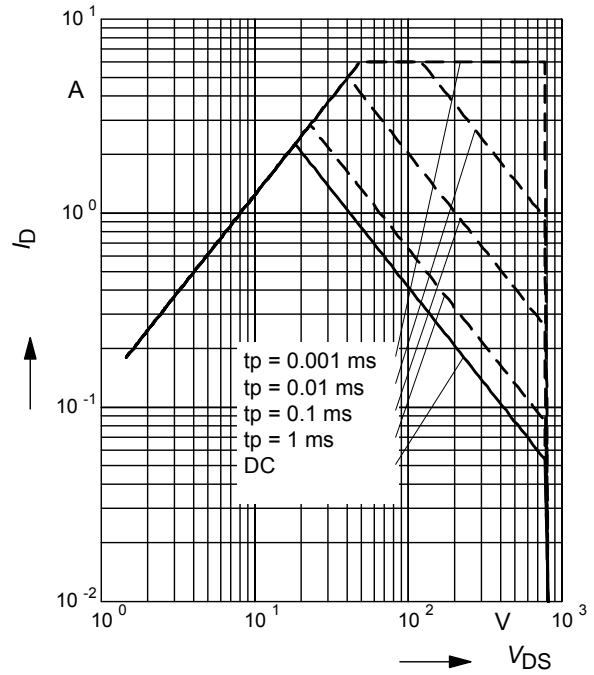
$P_{tot} = f(T_C)$



2 Safe operating area

$I_D = f(V_{DS})$

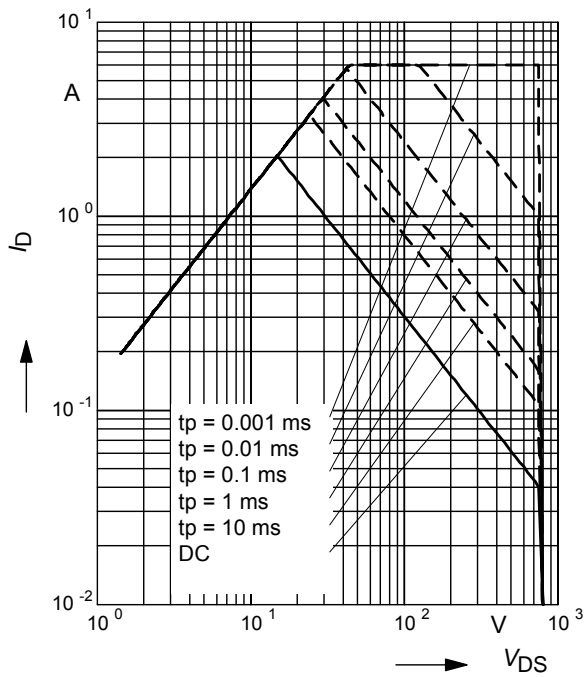
parameter : $D = 0, T_C = 25^\circ\text{C}$



3 Safe operating area FullPAK

$I_D = f(V_{DS})$

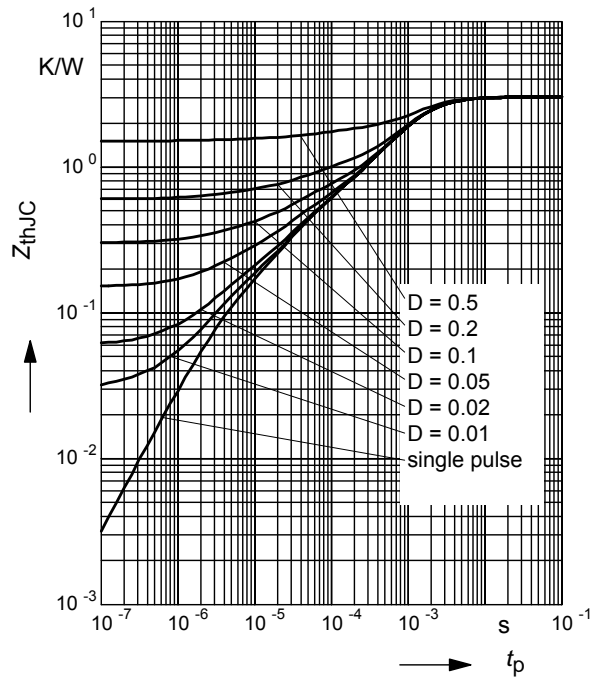
parameter: $D = 0, T_C = 25^\circ\text{C}$



4 Transient thermal impedance

$Z_{thJC} = f(t_p)$

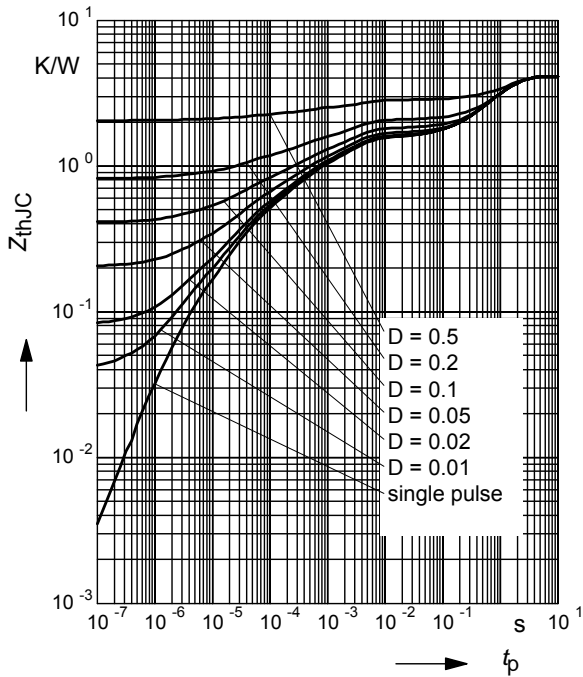
parameter: $D = t_p/T$



5 Transient thermal impedance FullPAK

$$Z_{thJC} = f(t_p)$$

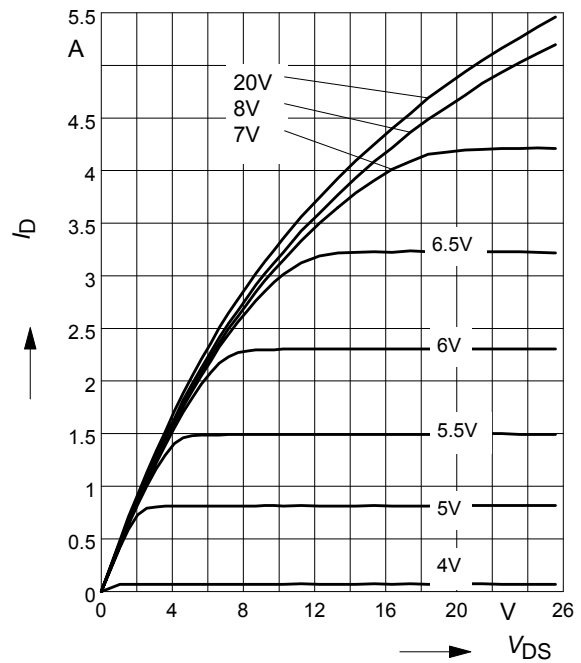
parameter: $D = t_p/t$



6 Typ. output characteristic

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

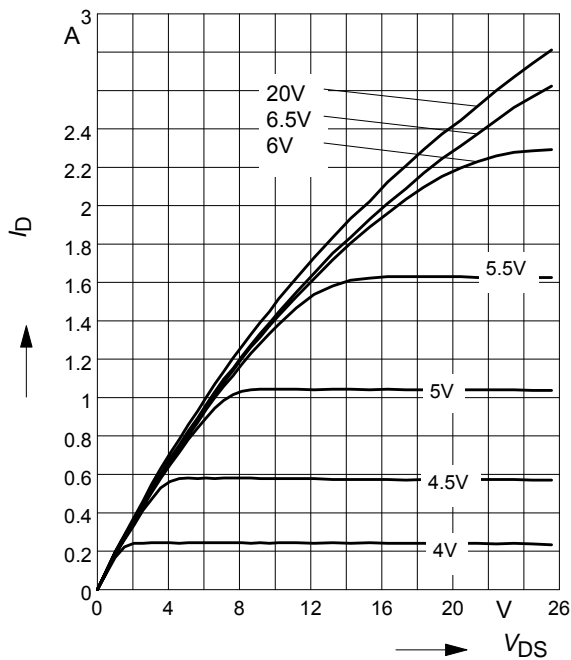
parameter: $t_p = 10 \mu\text{s}, V_{GS}$



7 Typ. output characteristic

$$I_D = f(V_{DS}); T_j = 150^\circ\text{C}$$

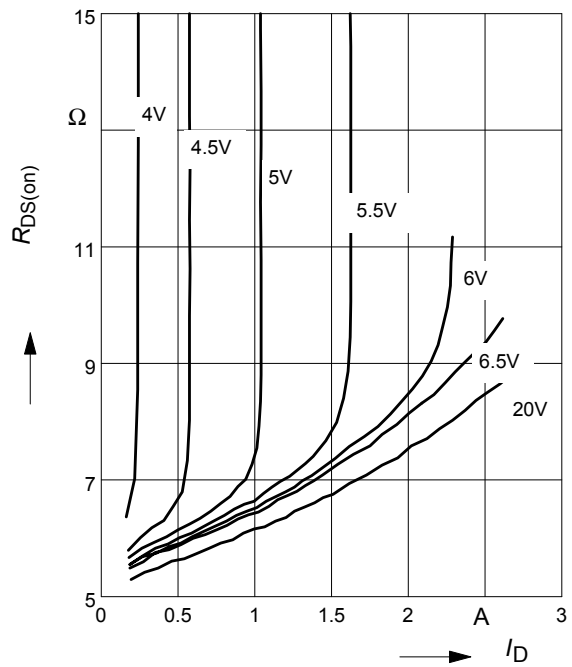
parameter: $t_p = 10 \mu\text{s}, V_{GS}$



8 Typ. drain-source on resistance

$$R_{DS(on)} = f(I_D)$$

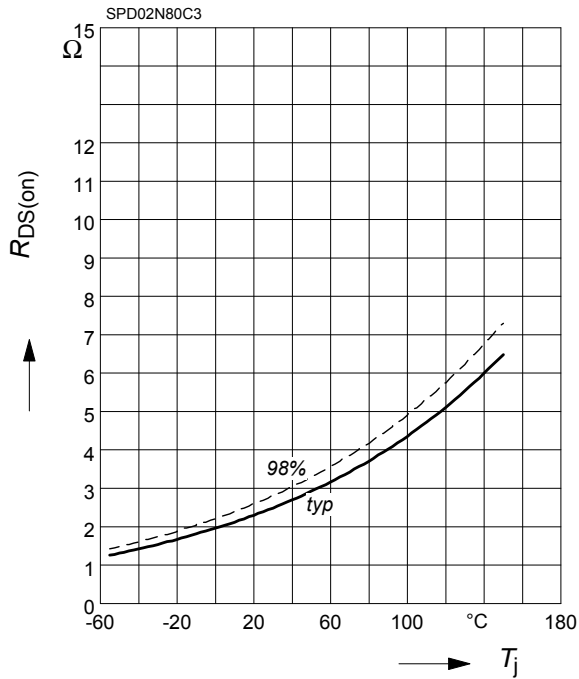
parameter: $T_j = 150^\circ\text{C}, V_{GS}$



9 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

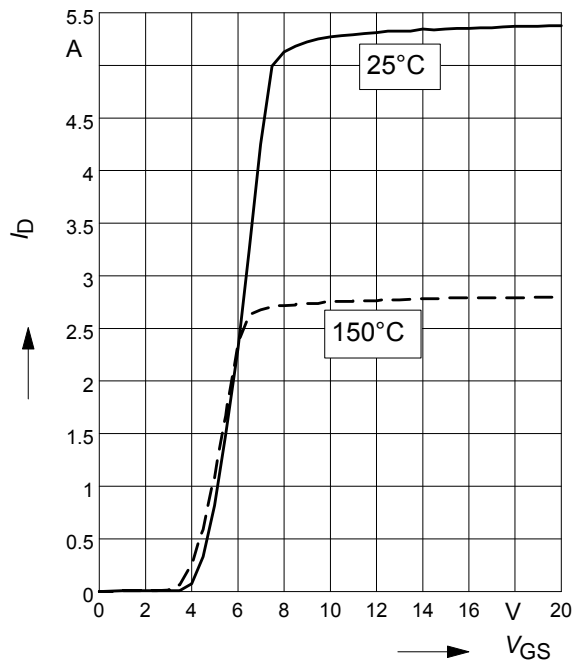
parameter : $I_D = 1.2 \text{ A}$, $V_{GS} = 10 \text{ V}$



10 Typ. transfer characteristics

$$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$

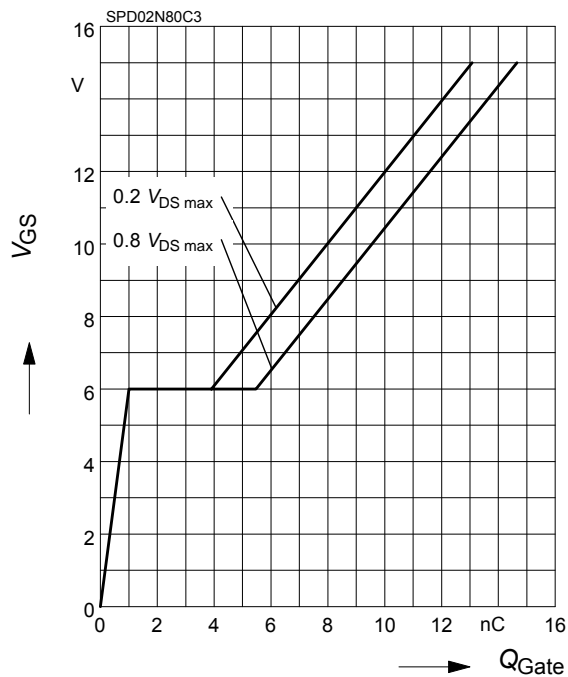
parameter: $t_p = 10 \mu\text{s}$



11 Typ. gate charge

$$V_{GS} = f(Q_{Gate})$$

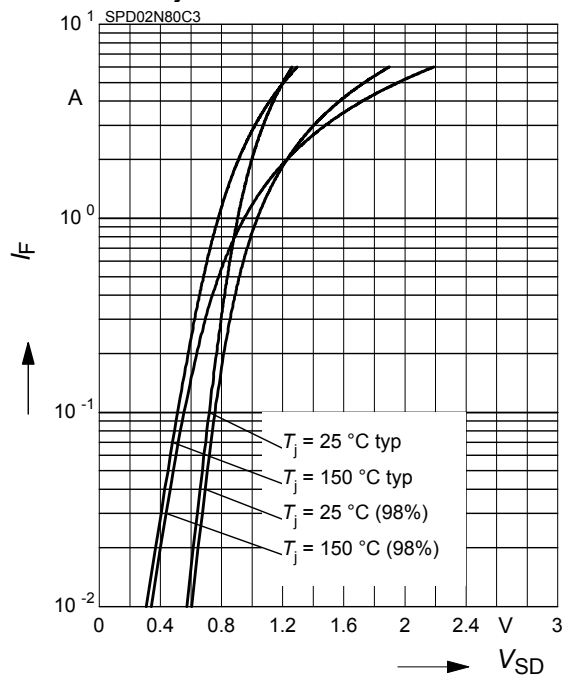
parameter: $I_D = 2 \text{ A}$ pulsed



12 Forward characteristics of body diode

$$I_F = f(V_{SD})$$

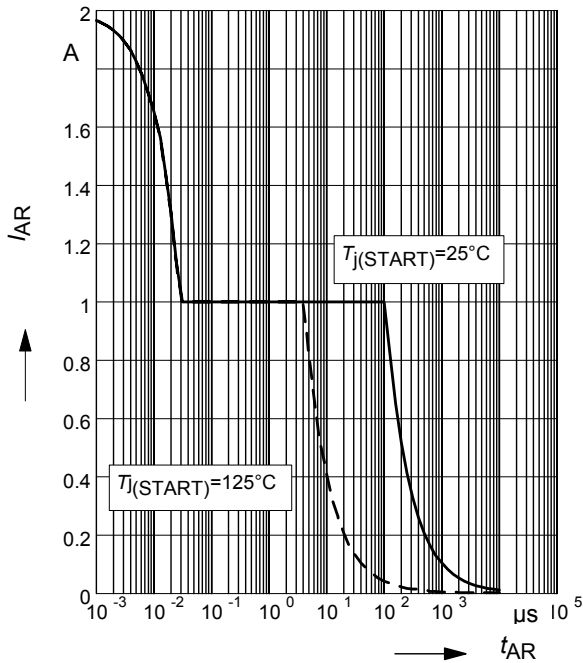
parameter: $T_j, t_p = 10 \mu\text{s}$



13 Avalanche SOA

$I_{AR} = f(t_{AR})$

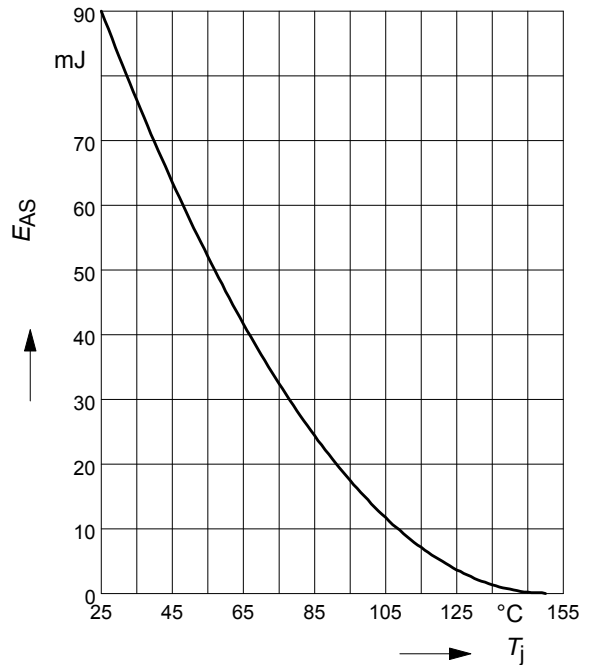
par.: $T_j \leq 150\text{ }^\circ\text{C}$



14 Avalanche energy

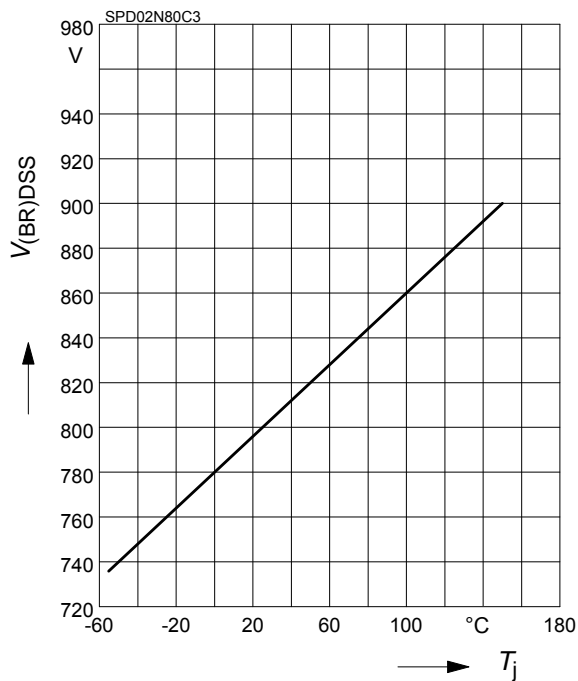
$E_{AS} = f(T_j)$

par.: $I_D = 1\text{ A}$, $V_{DD} = 50\text{ V}$



15 Drain-source breakdown voltage

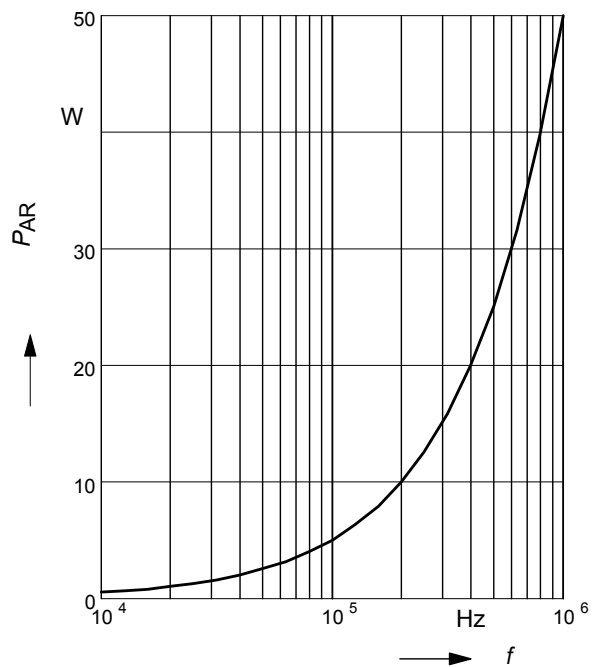
$V_{(BR)DSS} = f(T_j)$



16 Avalanche power losses

$P_{AR} = f(f)$

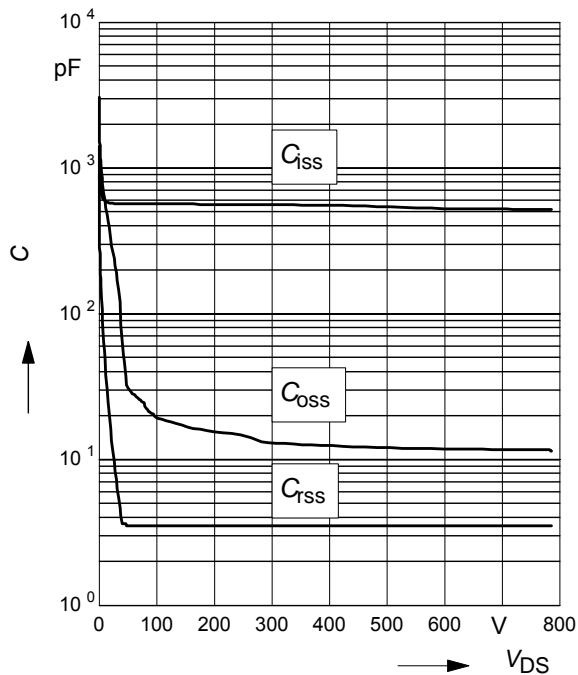
parameter: $E_{AR} = 0.05\text{ mJ}$



17 Typ. capacitances

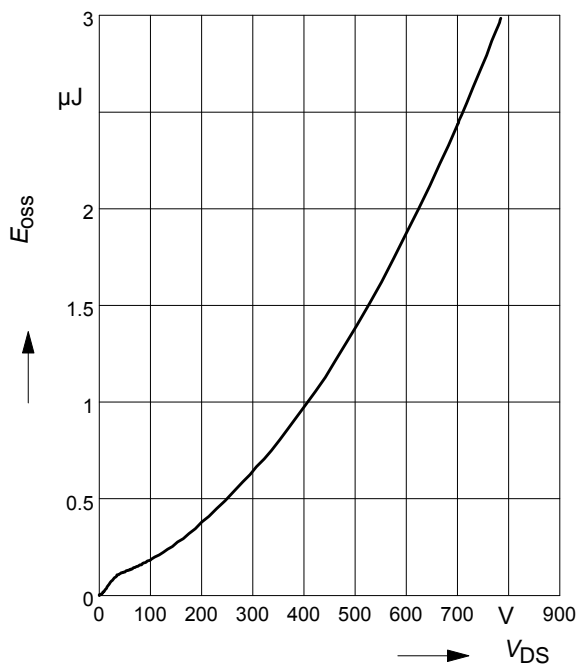
$$C = f(V_{DS})$$

parameter: $V_{GS}=0V, f=1\text{ MHz}$

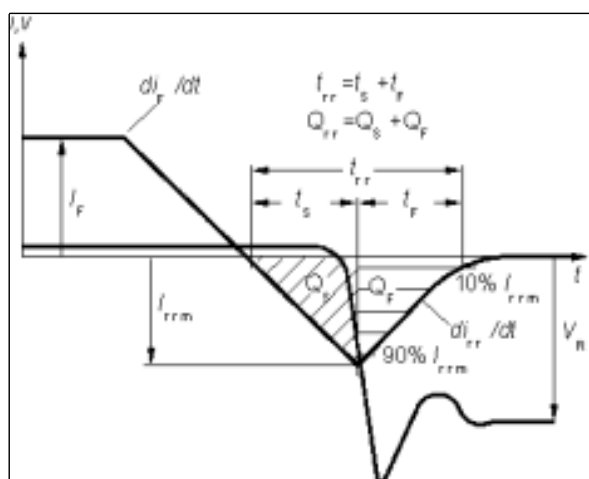


18 Typ. C_{oss} stored energy

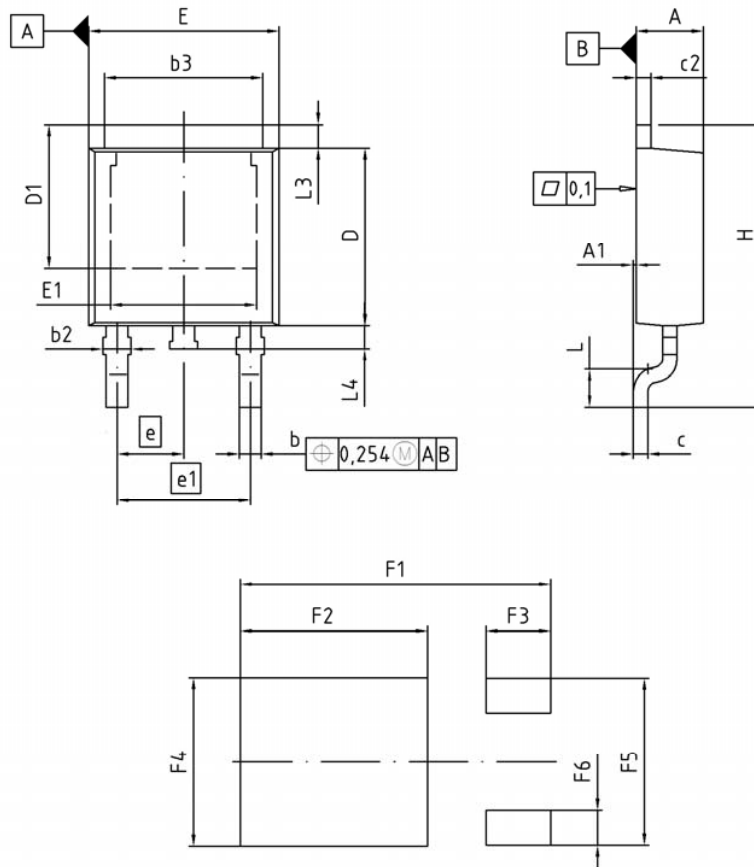
$$E_{oss} = f(V_{DS})$$



Definition of diodes switching characteristics



PG-TO252-3-1, PG-TO252-3-11, PG-TO252-3-21 (D-PAK)



| DIM | MILLIMETERS | | INCHES | |
|-----|-------------|-------|--------|-------|
| | MIN | MAX | MIN | MAX |
| A | 2.16 | 2.41 | 0.085 | 0.095 |
| A1 | 0.00 | 0.15 | 0.000 | 0.006 |
| b | 0.64 | 0.89 | 0.025 | 0.035 |
| b2 | 0.65 | 1.15 | 0.026 | 0.045 |
| b3 | 5.00 | 5.50 | 0.197 | 0.217 |
| c | 0.46 | 0.60 | 0.018 | 0.024 |
| c2 | 0.46 | 0.98 | 0.018 | 0.039 |
| D | 5.97 | 6.22 | 0.235 | 0.245 |
| D1 | 5.02 | 5.84 | 0.198 | 0.230 |
| E | 6.40 | 6.73 | 0.252 | 0.265 |
| E1 | 4.70 | 5.21 | 0.185 | 0.205 |
| e | 2.29 | | 0.090 | |
| e1 | 4.57 | | 0.180 | |
| N | 3 | | 3 | |
| H | 9.40 | 10.48 | 0.370 | 0.413 |
| L | 1.18 | 1.70 | 0.046 | 0.067 |
| L3 | 0.90 | 1.25 | 0.035 | 0.049 |
| L4 | 0.51 | 1.00 | 0.020 | 0.039 |
| F1 | 10.50 | 10.70 | 0.413 | 0.421 |
| F2 | 6.30 | 6.50 | 0.248 | 0.256 |
| F3 | 2.10 | 2.30 | 0.083 | 0.091 |
| F4 | 5.70 | 5.90 | 0.224 | 0.232 |
| F5 | 5.66 | 5.86 | 0.223 | 0.231 |
| F6 | 1.10 | 1.30 | 0.043 | 0.051 |

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